



US009348694B1

(12) **United States Patent**  
**Nassie**

(10) **Patent No.:** **US 9,348,694 B1**  
(45) **Date of Patent:** **May 24, 2016**

(54) **DETECTING AND MANAGING BAD COLUMNS**

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(\*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 32 days.

Search Report of PCT Patent Application WO 2009/118720 A3, Mar. 4, 2010.

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(21) Appl. No.: **14/050,264**

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(22) Filed: **Oct. 9, 2013**

(74) *Attorney, Agent, or Firm* — Reches Patents

(51) **Int. Cl.**

**G06F 11/10** (2006.01)  
**G11C 29/00** (2006.01)  
**G11C 29/04** (2006.01)  
**G11C 29/12** (2006.01)  
**G06F 12/02** (2006.01)  
**G11C 29/56** (2006.01)  
**G11C 29/44** (2006.01)

(52) **U.S. Cl.**

CPC ..... **G06F 11/1068** (2013.01); **G06F 12/0246**  
(2013.01); **G11C 29/00** (2013.01); **G11C 29/04**  
(2013.01); **G11C 29/12** (2013.01); **G11C**  
**29/56008** (2013.01); **G11C 2029/1208**  
(2013.01); **G11C 2029/4402** (2013.01); **G11C**  
**2029/5606** (2013.01)

(58) **Field of Classification Search**

CPC ..... **G11C 29/00**; **G11C 29/04**; **G11C 29/12**;  
**G11C 2029/1208**; **G11C 2029/4402**; **G11C**  
**29/56008**; **G11C 2029/5606**; **G06F 11/1068**;  
**G06F 12/0246**  
USPC ..... **714/718, 719, 723, 773, 704, 48**;  
**365/200, 201; 711/103**

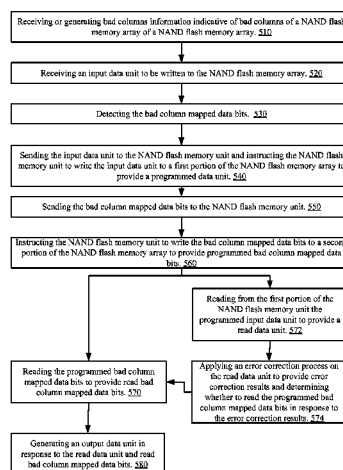
See application file for complete search history.

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**ABSTRACT**

A system, computer readable medium and a method. The system includes a memory controller that comprises a control circuit and an interface. The memory controller is arranged to receive or generate bad columns information indicative of bad columns of the NAND flash memory array; wherein the bad columns information has a column resolution. The memory controller is arranged to receive an input data unit to be written to the NAND flash memory array; wherein the input data unit comprises bad column mapped data bits that are mapped to flash memory cells that belong to bad columns of the NAND flash memory array. The interface is arranged to send the input data unit to the NAND flash memory unit; instruct the NAND flash memory unit to write the input data unit to a first portion of the NAND flash memory array to provide a programmed data unit; send the bad column mapped data bits to the NAND flash memory unit; and instruct the NAND flash memory unit to write the bad column mapped data bits to a second portion of the NAND flash memory array to provide programmed bad column mapped data bits.

**19 Claims, 12 Drawing Sheets**



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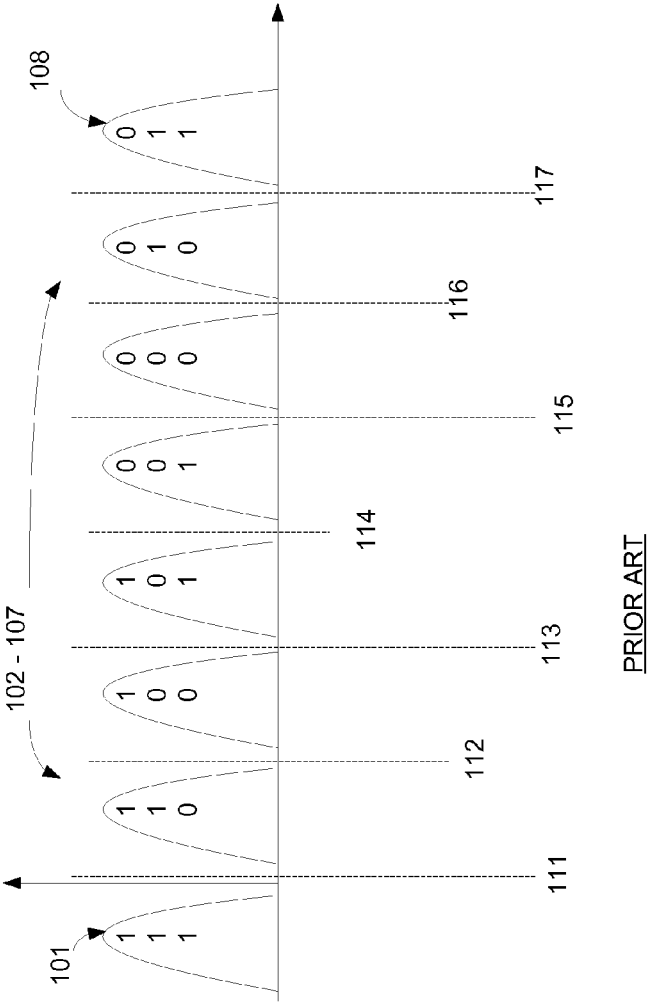
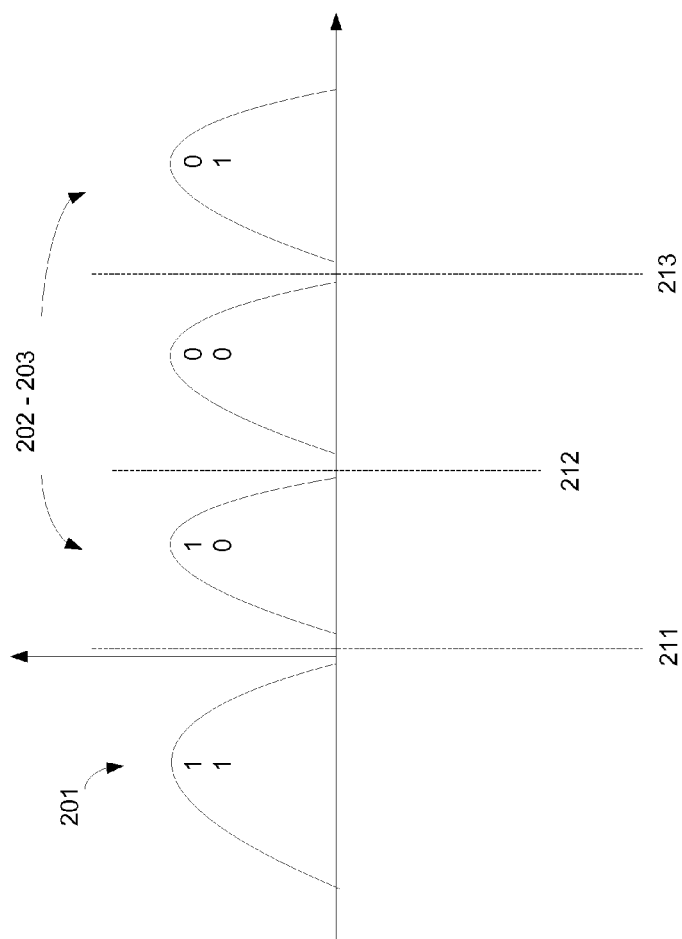
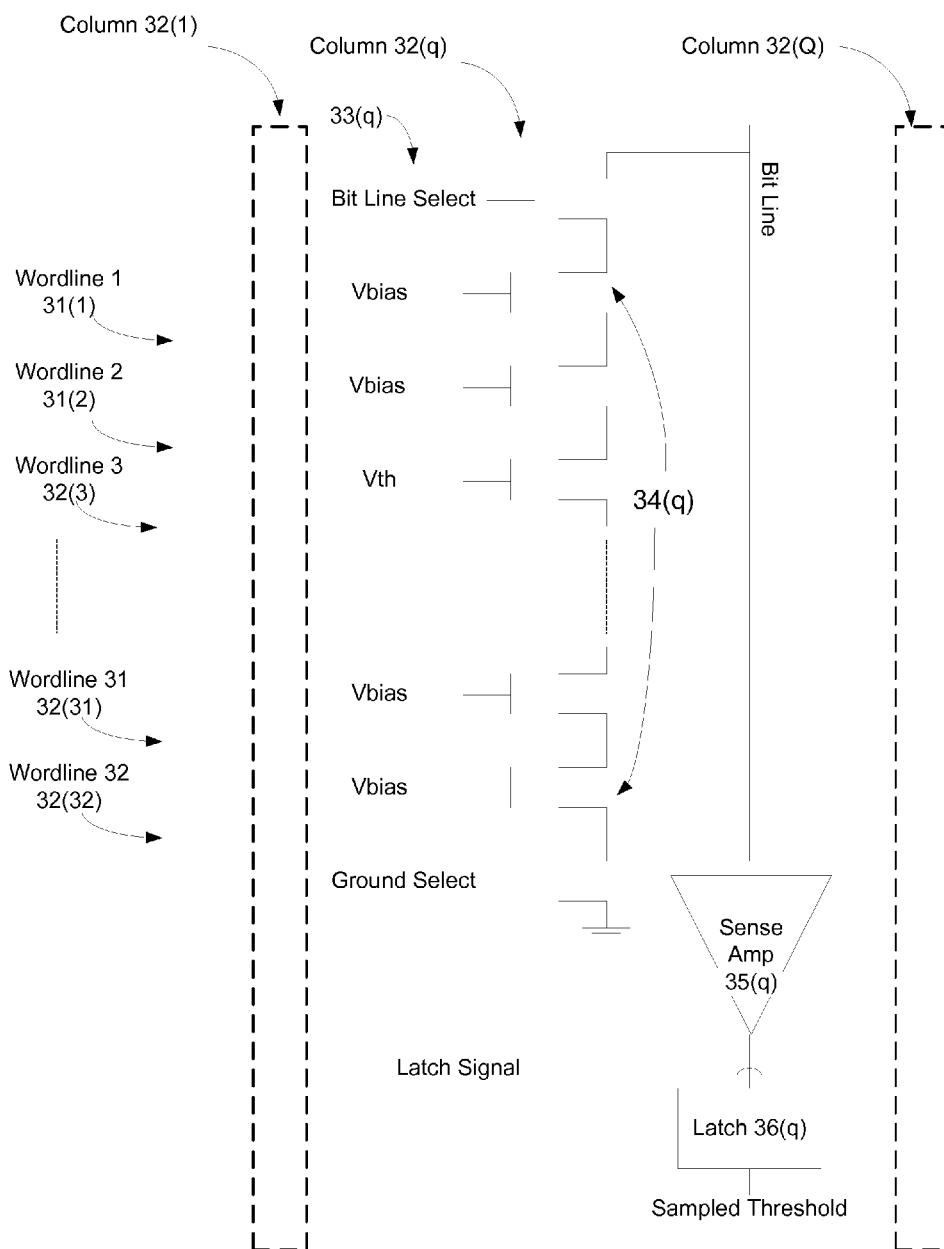


FIG. 1



PRIOR ART

FIG. 2



30

FIG. 3

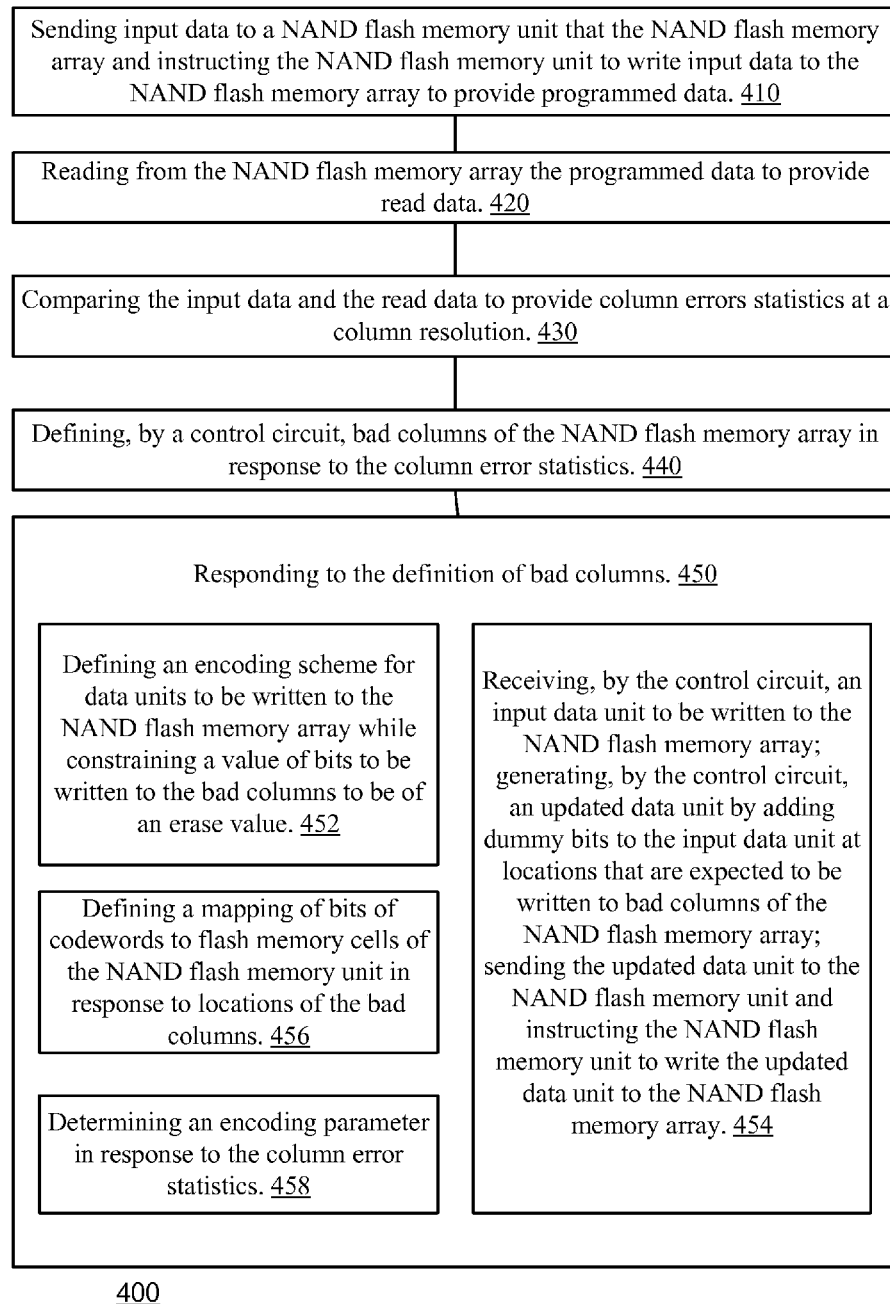


FIG. 4

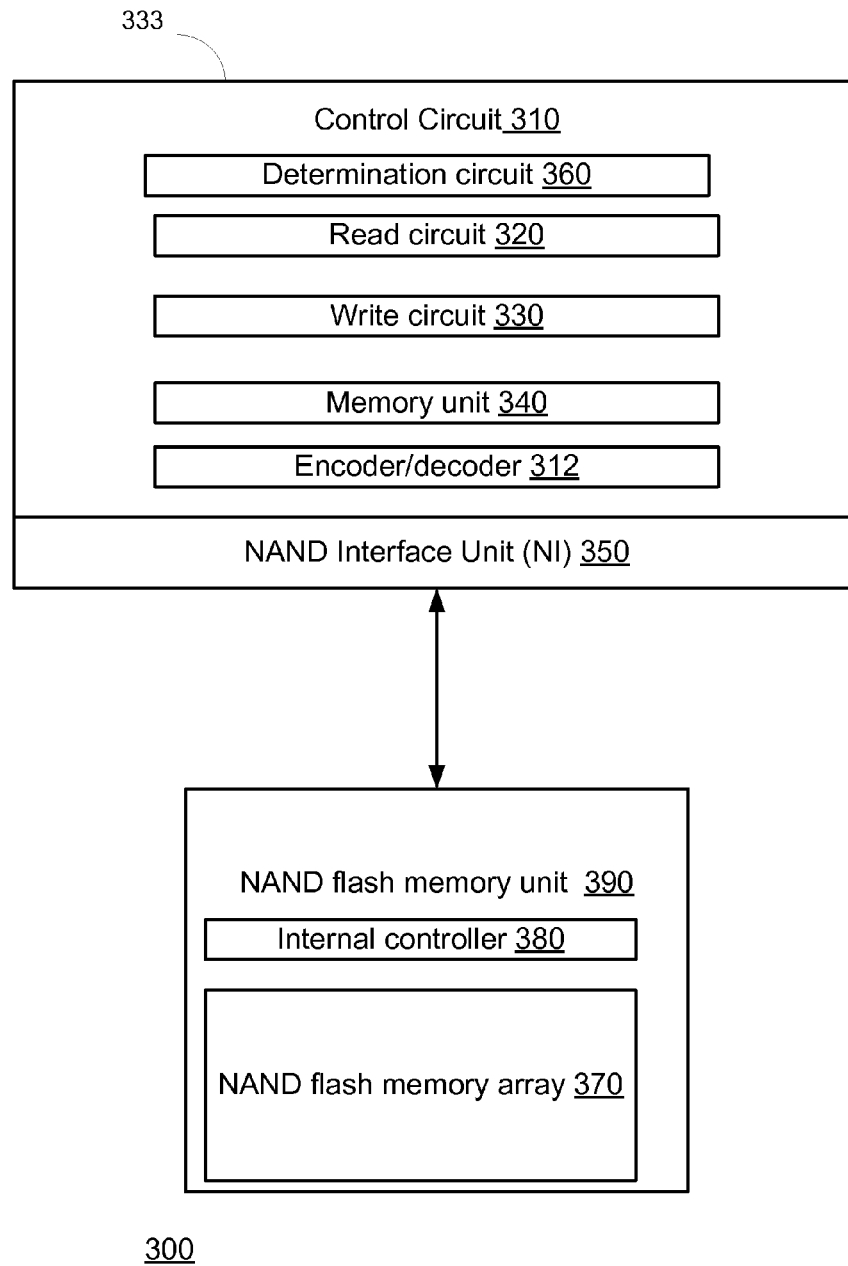
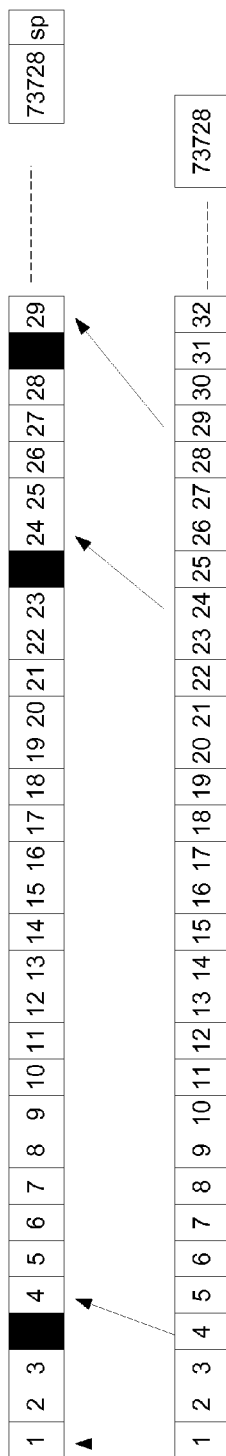


FIG. 5

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Concatenated  
Codewords 60

FIG. 6

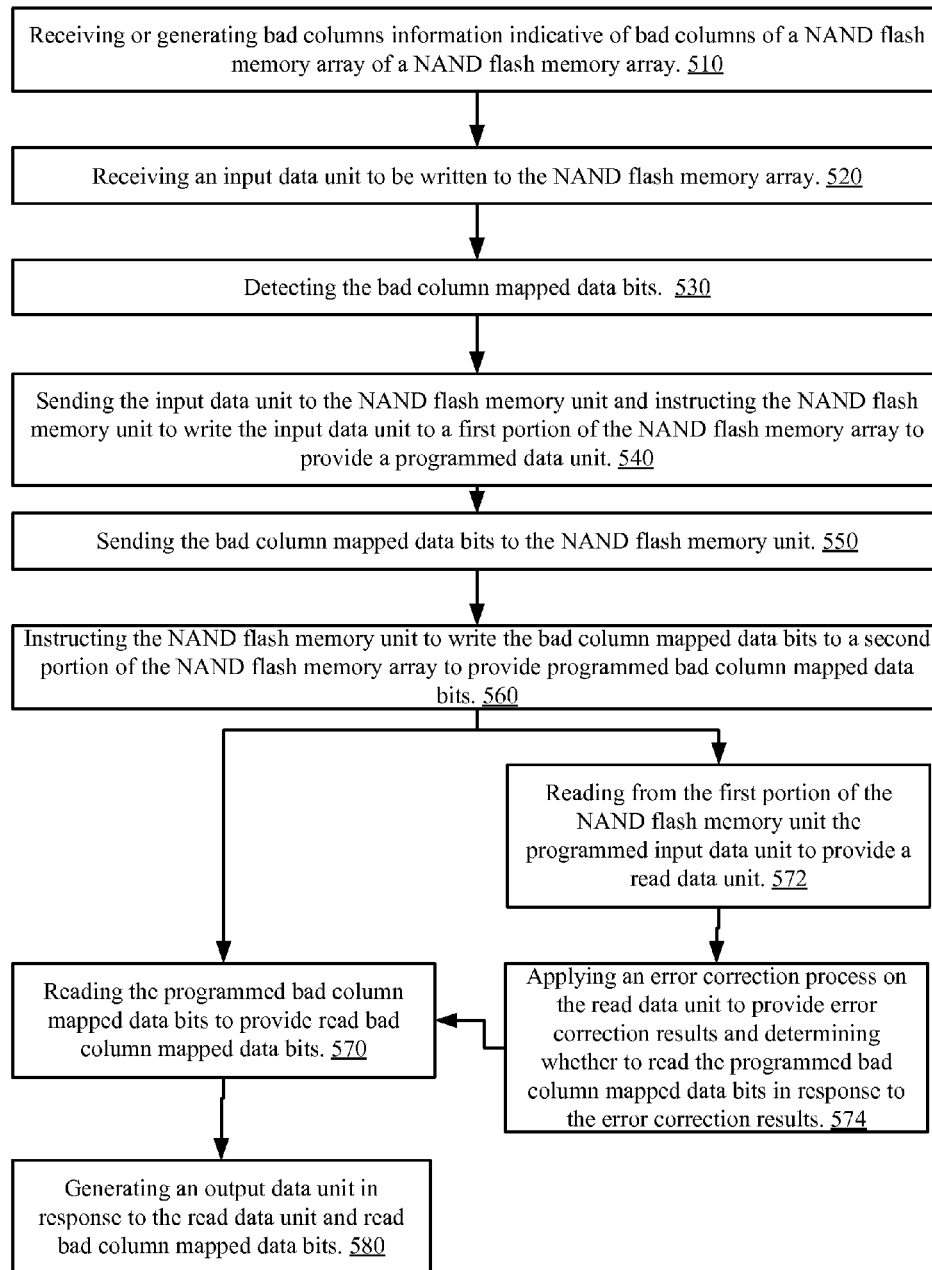
500

FIG. 7

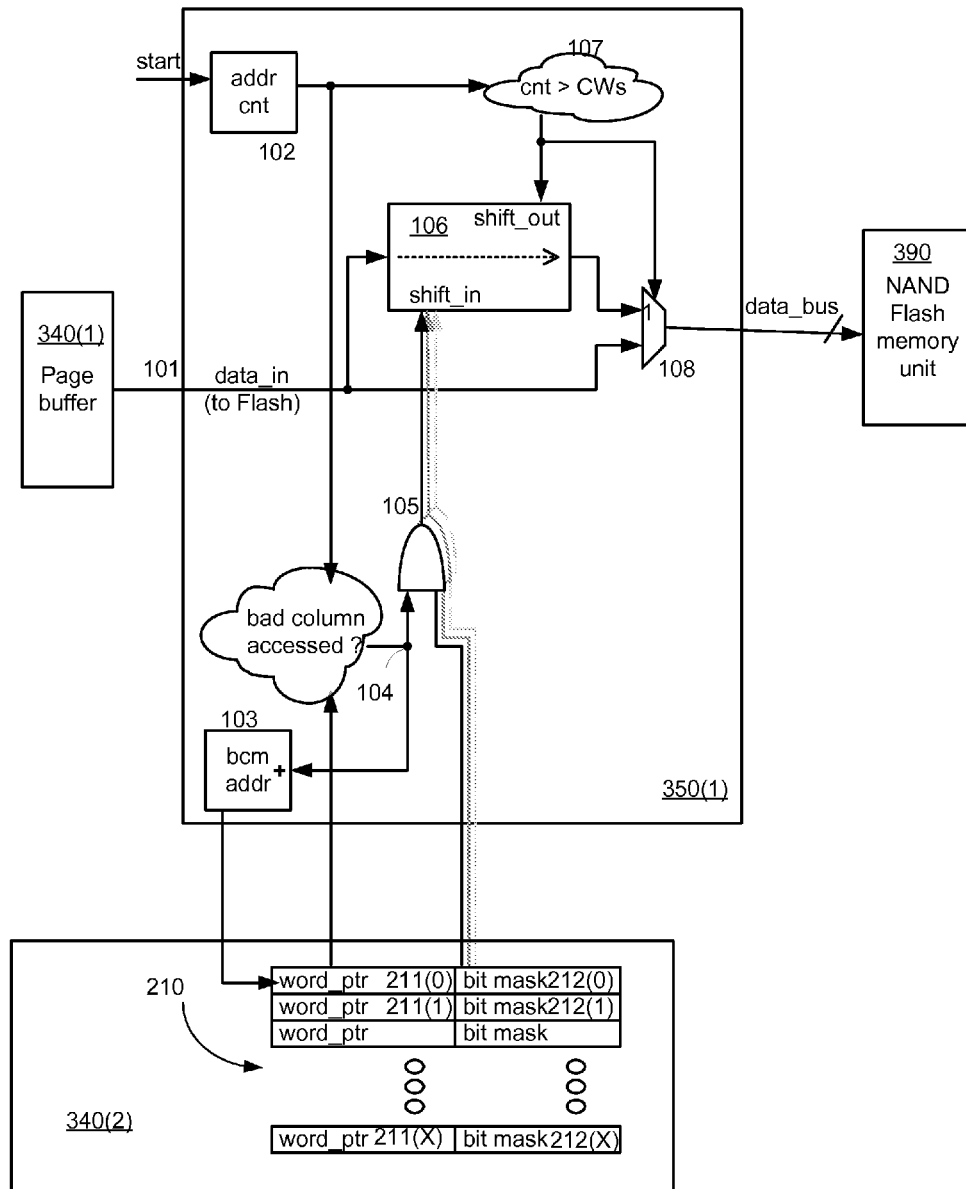


FIG. 8

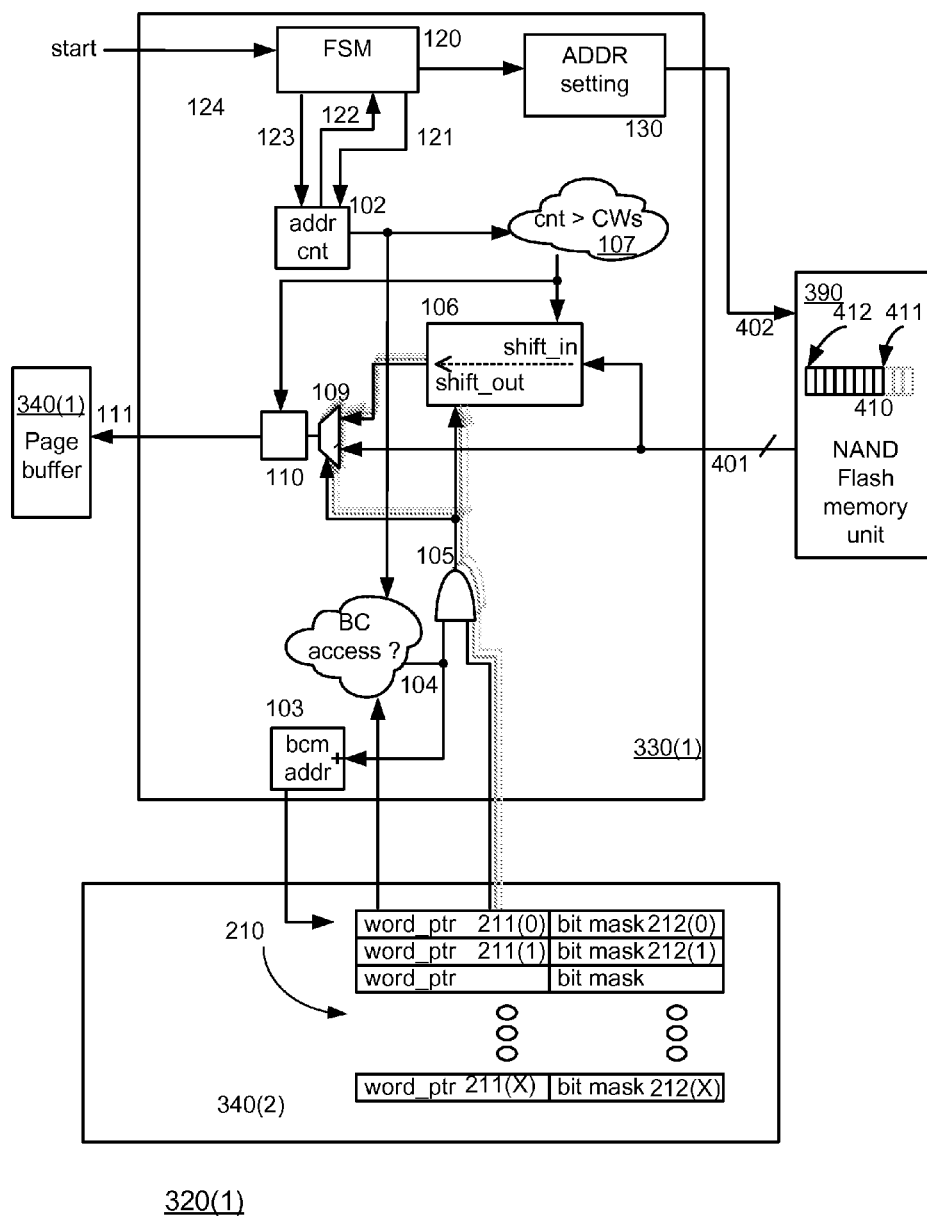


FIG. 9

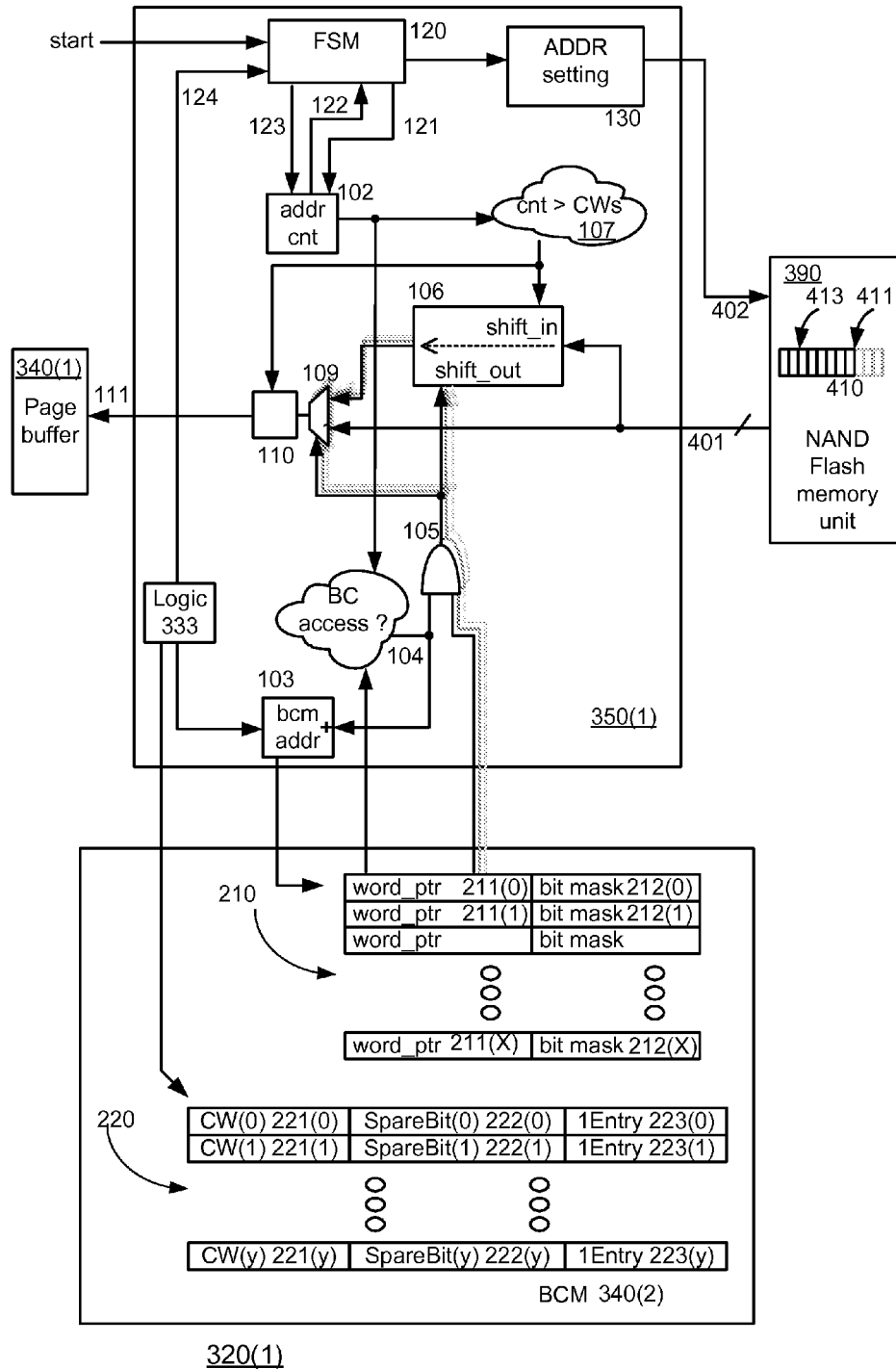


FIG. 10

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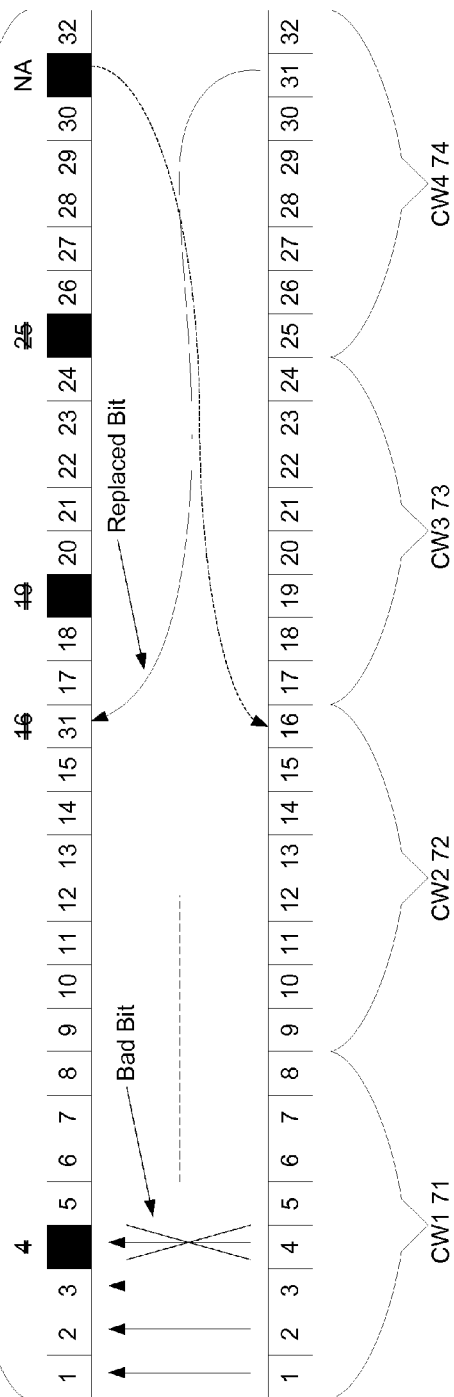


FIG. 11

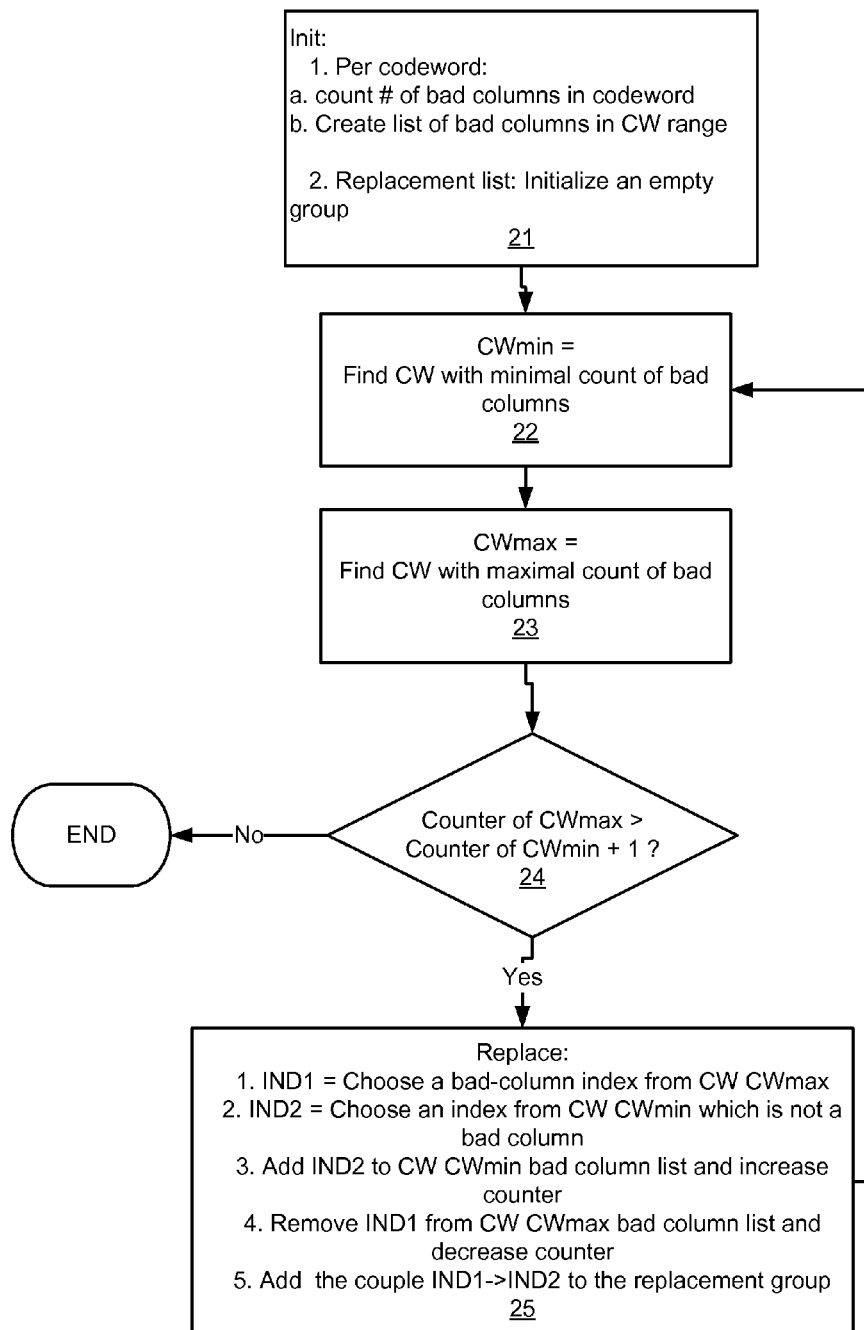
20

FIG. 12

1

## DETECTING AND MANAGING BAD COLUMNS

### CROSS REFERENCE TO RELATED APPLICATIONS

This application relates to a concurrently filed and co-pending U.S. patent application Ser. No. 14/050,249, entitled "Detecting and Managing Bad Columns" by Amir Nassie, owned by the assignee of this application and incorporated by reference herein in its entirety.

### BACKGROUND OF THE INVENTION

Nonvolatile flash memory devices store information in the form of charge in a flash memory cell. A flash memory cell has a CMOS transistor with an additional floating metal gate between the substrate and the transistors gate. The charge is stored in the floating gate and is injected to the floating gate during an operation known as programming. The charge may be removed during an operation known as an erase operation.

As the charge in the floating gate may vary contiguously, it is possible to store more than just one bit per flash transistor by using several charge levels to symbolize different sequences of bits.

FIG. 1 demonstrates a voltage level distribution for a 3 bpc (bits per cell) flash memory cell. The voltage level distribution includes eight lobes **101-108**. Each lobe represents a 3-bit value.

The voltage level distributions of FIG. 1 illustrates non-overlapping lobes, however this is only schematic, and in practical cases the lobes may overlap. The reason for overlapping may be intentional for obtaining high programming speed, or due to the retention effect. For floating gate devices, an "old" page, may introduce greater overlap between lobes than a new page, since after many program/erase (P/E) cycles there is accumulated trap charge, which is de-trapped over time. After a long duration, every lobe may have a larger standard deviation (std) and may have a different mean location. These effects are also known as retention.

The 3 bpc cell includes a most significant bit (MSB), a central significant bit (CSB) and a least significant bit (LSB). A physical page of flash memory module may store three logical pages. This physical page is programmed one logical page after the other. The programming includes various types of programming such as MSB programming (in which some of the cells are programmed to a single lobe and some are left in the erase state. At the end of this programming process only two lobes exists, the erase and the MSB lobes), a CSB programming (in which the erase lobe and the MSB lobe are each split into two lobes by further programming pulses, depending on the original state of each cell and the corresponding CSB bit. At the end of this step there are four lobes.) and a LSB programming (in which each of the four lobes is further split to create 8 lobes, overall). The logical pages are read by applying various types of read operations such as MSB read (in which a MSB threshold **114** is used), CSB read (in which two CSB thresholds **112** and **116** are used) and LSB read (in which four LSB thresholds **111**, **113**, **115** and **117** are used). FIG. 2 shows similar distributions for the case of 2 bpc devices.

A NAND Flash array (or block) is constructed from NAND Flash memory cells. The NAND Flash memory cells are grouped into columns (or strings). FIG. 3 shows a typical prior art portion **30** of a NAND flash memory array that includes thirty two lines (wordlines **31(1)-32(32)**) and multiple (Q) columns (**32(1)-32(Q)**). Once column **32(q)** is illus-

2

trated in further details—it shows the thirty two flash memory cells **34(q)** of the column, bit line select transistor and ground select transistor, and the voltages **33(q)** supplied to the transistors and flash memory cells (Bit Line Select, Vbias, Vth). Column **32(q)** is connected to sense amplifier **35(q)**, that in turn is connected to latch **36(q)**. A string (column) is duplicated many times (for example Q=34560 times) in a block and includes several (for example—thirty two) flash memory cells. Each of the flash memory cells is associated with a different wordline (or row) which connects all of the corresponding cells in the other strings of the block. When a block is chosen, each string is connected to a corresponding bitline by turning on the Bit Line Select and the Ground Select transistors. When a read operation is performed, a sense amplifier is connected to the bit-line and after allowing some time (say 25 uS) for the bit-line voltage to settle, the result is stored by a latch.

In order to measure the charge in a certain cell within a string, all other cells are switched on by applying a high voltage on their gates (given by Vbias) and a comparison voltage, Vth, is applied to the gate of the selected cell. If the cell is charged and Vth is not high enough, the gate will not allow current to flow and the sense-amplifier will output a "0". On the other hand, if the cell is not charge or Vth is high enough, current will flow and the sense-amplifier will output a "1". Different schemes may exist where the cell being samples is biased with a constant voltage (say Vcc) but in the sense-amplifier a comparison against a reference string is performed which reference value may be determined by some external voltage, Vth.

The above sampling technique holds when a bit may be obtained only through a single threshold comparison. When more than a single threshold comparison is required, the above procedure may be performed for each threshold and the results may then be combined. Alternatively, several sense-amplifiers may be used simultaneously, each one compares against a different threshold, and the results are then combined to yield the required bit value.

All cells in a wordline (physical page) are programmed simultaneously and read simultaneously. In case of MLC or TLC, the programming of a wordline is divided into two or three stages, referred to as MSB, CSB and LSB page programming stages.

Due to manufacturing defects, some of the columns may not operate properly. In that case, NAND manufacturers, allocate spare strings which are used to replace the defective strings. The replacement is done during the manufacturing process, where the bad columns are detected and internal circuitry is used to remap the spare strings to replace. Typically, the replacement is not very efficient as entire bytes or words (16 bits) are replaced even if a single column was bad. That is, the columns are divided into chunks of 8 or 16 columns and the replacement is done on an entire chunk.

Alternatively, some manufacturers do not replace the bad columns and leave the task to the memory controller that controls the NAND Flash. That is, more strings are allocated on a NAND array to allow some spare strings for replacement. However, the re placements is not done at the NAND array level but rather, bad columns are handled by the controller instead.

### SUMMARY

A method, a system and a non-transitory computer readable medium are provided for detecting and managing bad columns of a NAND flash memory array.

According to an embodiment of the invention a method may be provided and may include receiving or generating bad columns information indicative of bad columns of the NAND flash memory array; wherein the bad columns information has a column resolution; receiving an input data unit to be written to the NAND flash memory array; wherein the input data unit comprises bad column mapped data bits that are mapped to flash memory cells that belong to bad columns of the NAND flash memory array; sending the input data unit to the NAND flash memory unit and instructing the NAND flash memory unit to write the input data unit to a first portion of the NAND flash memory array to provide a programmed data unit; sending the bad column mapped data bits to the NAND flash memory unit; and instructing the NAND flash memory unit to write the bad column mapped data bits to a second portion of the NAND flash memory array to provide programmed bad column mapped data bits.

The first and second portions of the NAND flash memory array may belong to a same physical page of the NAND flash memory array.

The method may include storing the bad column mapped data bits at a bad column mapped memory unit of the memory controller.

The method may include detecting the bad column mapped data bits in response to a first data structure that maps flash memory cells of bad columns to locations of bad column mapped data bits within the input data unit.

The method may include storing at the flash memory unit a first data structure that maps flash memory cells of bad columns to locations of bad column mapped data bits and a second data structure that maps codewords to (i) content of the second portion of the NAND flash memory array and to (ii) entries of the first data structure.

The method may include reading from the first portion of the NAND flash memory unit the programmed input data unit to provide a read data unit; applying an error correction process on the read data unit to provide error correction results; and determining whether to read the programmed bad column mapped data bits in response to the error correction results.

The method may include reading the programmed bad column mapped data bits to provide read bad column mapped data bits; and generating an output data unit in response to the read data unit and read bad column mapped data bits.

The generating comprises replacing bits of the read data unit that were mapped to flash memory units of bad columns by read bad column mapped data bits.

The method may include detecting bits of the read data unit that were mapped to flash memory units of bad columns by accessing a first data structure that maps flash memory cells of bad columns to locations of bad column mapped data bits within the input data unit.

The read data unit is associated with a certain codeword out of multiple codewords; wherein the method comprise detecting bits of the read data unit that may belong to the certain codeword by accessing a first data structure that maps flash memory cells of bad columns to locations of bad column mapped data bits and by accessing a second data structure that maps codewords to (i) content of the second portion of the NAND flash memory array and to (ii) entries of the first data structure.

According to an embodiment of the invention there may be provided a non-transitory computer readable medium that includes instructions to be executed by a computer and cause the computer to perform stages that may include: receiving or generating bad columns information indicative of bad columns of a NAND flash memory array of a NAND flash memory unit; wherein the bad columns information has a

column resolution; receiving an input data unit to be written to the NAND flash memory array; wherein the input data unit comprises bad column mapped data bits that are mapped to flash memory cells that may belong to bad columns of the NAND flash memory array; sending the input data unit to the NAND flash memory unit and instructing the NAND flash memory unit to write the input data unit to a first portion of the NAND flash memory array to provide a programmed data unit; sending the bad column mapped data bits to the NAND flash memory unit; and instructing the NAND flash memory unit to write the bad column mapped data bits to a second portion of the NAND flash memory array to provide programmed bad column mapped data bits.

According to an embodiment of the invention there may be provided a system that may include a memory controller that may include a control circuit and an interface. The control circuit may be arranged to receive or generate bad columns information indicative of bad columns of the NAND flash memory array. The bad columns information has a column resolution. The control circuit may be arranged to receive an input data unit to be written to the NAND flash memory array. The input data unit includes bad column mapped data bits that are mapped to flash memory cells that may belong to bad columns of the NAND flash memory array. The interface may be arranged to: send the input data unit to the NAND flash memory unit; instruct the NAND flash memory unit to write the input data unit to a first portion of the NAND flash memory array to provide a programmed data unit; send the bad column mapped data bits to the NAND flash memory unit; and instruct the NAND flash memory unit to write the bad column mapped data bits to a second portion of the NAND flash memory array to provide programmed bad column mapped data bits.

The first and second portions of the NAND flash memory array may belong to a same physical page of the NAND flash memory array.

The control circuit may be arranged to store the bad column mapped data bits at a bad column mapped memory unit of the memory controller.

The control circuit may be arranged to detect the bad column mapped data bits in response to a first data structure that maps flash memory cells of bad columns to locations of bad column mapped data bits within the input data unit.

The control circuit may be arranged to store at the flash memory unit a first data structure that maps flash memory cells of bad columns to locations of bad column mapped data bits and a second data structure that maps codewords to (i) content of the second portion of the NAND flash memory array and to (ii) entries of the first data structure.

The control circuit may be arranged to read from the first portion of the NAND flash memory unit the programmed input data unit to provide a read data unit; apply an error correction process on the read data unit to provide error correction results; and determine whether to read the programmed bad column mapped data bits in response to the error correction results.

The control circuit may be arranged to read the programmed bad column mapped data bits to provide read bad column mapped data bits; and generate an output data unit in response to the read data unit and read bad column mapped data bits.

The control circuit may be arranged to generate the output data unit by replacing bits of the read data unit that were mapped to flash memory units of bad columns by read bad column mapped data bits.

The control circuit may be arranged to detect bits of the read data unit that were mapped to flash memory units of bad

columns by accessing a first data structure that maps flash memory cells of bad columns to locations of bad column mapped data bits within the input data unit.

The read data unit is associated with a certain codeword out of multiple codewords; wherein the control circuit may be arranged to detect bits of the read data unit that may belong to the certain codeword by accessing a first data structure that maps flash memory cells of bad columns to locations of bad column mapped data bits and by accessing a second data structure that maps codewords to (i) content of the second portion of the NAND flash memory array and to (ii) entries of the first data structure.

#### BRIEF DESCRIPTION OF THE DRAWINGS

The subject matter regarded as the invention is particularly pointed out and distinctly claimed in the concluding portion of the specification. The invention, however, both as to organization and method of operation, together with objects, features, and advantages thereof, may best be understood by reference to the following detailed description when read with the accompanying drawings in which:

FIG. 1 illustrates a prior art voltage threshold distribution;

FIG. 2 illustrates a prior art voltage threshold distribution;

FIG. 3 illustrates a prior art portion of a NAND flash memory array;

FIG. 4 illustrates a method according to an embodiment of the invention;

FIG. 5 illustrates a system according to an embodiment of the invention;

FIG. 6 illustrates an input data unit and an updated data unit generated by applying a bit skipping scheme according to an embodiment of the invention;

FIG. 7 illustrates a method according to an embodiment of the invention;

FIG. 8 illustrates a portion of a write circuit of a memory controller according to an embodiment of the invention;

FIG. 9 illustrates a portion of a read circuit of a memory controller according to an embodiment of the invention;

FIG. 10 illustrates a portion of a read circuit of a memory controller according to an embodiment of the invention;

FIG. 11 illustrates a mapping of codewords to flash memory cells and an updated mapping of codewords to flash memory cells according to an embodiment of the invention; and

FIG. 12 illustrates a method according to an embodiment of the invention.

It will be appreciated that for simplicity and clarity of illustration, elements shown in the figures have not necessarily been drawn to scale. For example, the dimensions of some of the elements may be exaggerated relative to other elements for clarity. Further, where considered appropriate, reference numerals may be repeated among the figures to indicate corresponding or analogous elements.

#### DETAILED DESCRIPTION OF THE DRAWINGS

In the following detailed description, numerous specific details are set forth in order to provide a thorough understanding of the invention. However, it will be understood by those skilled in the art that the present invention may be practiced without these specific details. In other instances, well-known methods, procedures, and components have not been described in detail so as not to obscure the present invention.

The subject matter regarded as the invention is particularly pointed out and distinctly claimed in the concluding portion of the specification. The invention, however, both as to orga-

nization and method of operation, together with objects, features, and advantages thereof, may best be understood by reference to the following detailed description when read with the accompanying drawings.

Because the illustrated embodiments of the present invention may for the most part, be implemented using electronic components and circuits known to those skilled in the art, details will not be explained in any greater extent than that considered necessary as illustrated above, for the understanding and appreciation of the underlying concepts of the present invention and in order not to obfuscate or distract from the teachings of the present invention.

Any reference in the specification to a method should be applied mutatis mutandis to a system capable of executing the method and should be applied mutatis mutandis to a non-transitory computer readable medium that stores instructions that once executed by a computer result in the execution of the method.

Any reference in the specification to a system should be applied mutatis mutandis to a method that may be executed by the system and should be applied mutatis mutandis to a non-transitory computer readable medium that stores instructions that may be executed by the system.

Any reference in the specification to a non-transitory computer readable medium should be applied mutatis mutandis to a system capable of executing the instructions stored in the non-transitory computer readable medium and should be applied mutatis mutandis to method that may be executed by a computer that reads the instructions stored in the non-transitory computer readable medium.

There are provided systems, methods and computer readable media for managing bad columns at a column resolution (on a column to column basis).

The term “controller” refers to a memory controller.

The term data unit refers to multiple data bits of any size. The data unit can include encoded data bit, decoded data bits or any type of data bits. A data unit can include a byte, a word, a page and the like. In some of the examples (for example—FIGS. 8-10) there is a reference of reading and writing words of a page. It is noted that this is just an example of data units.

The following description describes: (a) a scheme for detecting bad columns and how this information may be used during the decoding process; (b) two bad column replacement schemes; (c) a hardware design to implement one of the bad column replacement scheme; (d) spreading the bad columns across several codewords to reduce a possible uneven distribution of bad columns in portions of a NAND flash memory array allocated for storing the codewords; (e) and how code parameters may be designed modified to handle bad columns and consider the probability of their occurrence.

#### Bad Columns Detection

Some NAND flash units that do not replace the bad columns internally, allow the controller to read back the chunk location (byte/word) of each bad column.

However, this has two drawbacks. First, there is no distinction between one column and another within the chunk and thus all columns are discarded (bad or good). Secondly, there is no distinction in the severity of how bad is the column. It may be that some columns are declared bad but that is because they are more prone to errors. Such columns may still be used for carrying data but may be given lesser reliability.

Therefore, there is provided an alternative method for detecting bad columns. An erase block is programmed with random data and the its content is read back. The programmed data is then compared to the data read back and a page sized vector (i.e. number of values is equivalent to the number of

columns in a page) is used to count the number of errors that were detected per each column.

As an example consider a TLC device where each block has 64 rows and 192 pages. To create this vectors we nullify it at first and for each page being read, we compare it to the original data and add 1's to the vector at the locations corresponding to the error location.

We can then detect bad columns rather easily. We set a threshold (e.g. 20, in the previous example) such that if the vectors contain a value higher than that, the column is declared bad. For TLC devices, we can also do that for each page type separately by creating 3 such sum vectors and repeating the procedure above per page, using a different vector, depending on the page type.

Note that we can also obtain more refined information than just if the column was bad or not. The value of the vector may be used as a reliability indicator for a decoder. For example, returning to the example above: a block with 192 pages. The reliability indicator may be defined as the ratio  $LLR = \text{Log}(\text{value}/(192 - \text{value}))$ . This can then be used in conjunction with an LDPC code or any other coding scheme which decoder can make use of such log likelihood ratios.

Such information can also be used in conjunction with coding schemes which decoder allows decoding inputs with erasures. That is a decoding scheme which obtains per each bit 3 values: 0, 1 and Erasure. All columns which LLR above was between two given values can be assigned the Erasure value and the others 0 or 1, depending on the read value. BCH codes can also be decoded using erasure information. Other codes are LDPC, turbo-codes and more.

FIG. 4 illustrates method 400 according to an embodiment of the invention.

The method is for detecting bad columns of a NAND flash memory array.

Method 400 may start by stage 410 of sending input data to a NAND flash memory unit that may include the NAND flash memory array and instructing the NAND flash memory unit to write input data to the NAND flash memory array to provide programmed data.

Stage 410 may be followed by stage 420 of reading from the NAND flash memory array the programmed data to provide read data.

Stage 420 may be followed by stage 430 of comparing the input data and the read data to provide column errors statistics at a column resolution. The column error statistics provide information on the number of errors per column. An error is detected as a mismatch between a value of an input data bit and a corresponding read data bit. The mismatch is associated with a column that includes the flash memory cell that stored the programmed data bit that corresponds to the read data bit and the input data bit.

Stage 430 may be followed by stage 440 of defining, by a memory controller, bad columns of the NAND flash memory array in response to the column error statistics.

The column errors statistics may be indicative of a number of errors per column. Stage 440 may include defining a column of the NAND flash memory array as a bad column if a number of errors associated with the column exceed an error threshold.

The column errors statistics is indicative of a number of errors per column and stage 440 may include assigning a reliability score per each column in response to a number of errors associated with the column. This reliability score can be used when determine what to program to flash memory cells of a bad column, when determining data reconstruction schemes and the like.

Stage 440 may be followed by stage 450 of responding to the definition of bad columns.

The responding may include applying any of the schemes disclosed in this application including, for example, determining encoding parameters, bit skipping, bit replacement, bad column spreading schemes or any bad column replacement schemes.

Stage 450 may include at least one out of stages 452, 454, 456 and 458.

Stage 452 may include defining an encoding scheme for data units to be written to the NAND flash memory array while constraining a value of bits to be written to the bad columns to be of an erase value.

Stage 454 may include bit skipping—receiving, by the memory controller, an input data unit to be written to the NAND flash memory array; generating, by the memory controller, an updated data unit by adding dummy bits to the input data unit at locations that are expected to be written to bad columns of the NAND flash memory array; and sending the updated data unit to the NAND flash memory unit and instructing the NAND flash memory unit to write the updated data unit to the NAND flash memory array. The value of a dummy bit to be written, instead a data bit, to a flash memory cell of a bad column equals a value of the data bit.

Stage 456 may include a bad column spreading scheme—defining a mapping of bits of codewords to flash memory cells of the NAND flash memory unit in response to locations of the bad columns.

The defining of the mapping reduces an effect of an uneven distribution of bad columns within NAND flash memory unit portions allocated for storing the codewords.

The mapping of bits of a codeword, is further responsive to a relationship between (a) a size (S1) of a NAND flash memory unit portion allocated for storing the codeword, and (b) a sum of (i) a size (S2) of the codeword and (ii) a number (N1) of flash memory cells that belong to a bad column within the NAND flash memory unit portion allocated for storing the codeword.

If  $S1 > S2 + N1$  there may not be a need to perform spreading and the entire codeword can be written only to flash memory cells of good columns. Nevertheless— $S1 - (S2 + N1)$  flash memory cells may be programmed with stuffing bits.

If  $S1 > S2 + N1$  then some bits may be lost.

Stage 456 may include swapping bits that belong to different codewords in response to an amount of bad columns and to a location of bad columns in NAND flash memory units portions initially allocated for storing the different codewords.

Stage 458 may include determining an encoding parameter in response to the column error statistics.

The encoding parameter may be a bit error rate of a code to be used for providing codewords. These codewords may be represented by one or more input data units.

The encoding parameter may be a number of redundancy bits to be allocated per codeword.

The number of redundancy bits may be determined to optimize a value of a function of (a) bad column distribution between different dies of the NAND flash memory unit and (b) a bit error rate function.

The determining may be responsive to column error statistics of different dies of NAND flash memory unit that are activated at a certain point in time.

Bad Columns Replacement Schemes

Another method of handling bad columns is not using them. This is generally supported by column replacement operation within the NAND Flash devices. However, as men-

tioned this replacement operation is rather coarse and works on entire chunks instead of a single string.

According to an embodiment of the invention it may be desirable to perform the replacement in a controller at the bit level. In general, before programming data into the NAND, codewords may be aggregated inside the NAND Flash controller until sufficient data is available to program a full NAND page. The NAND page data is then transferred to the NAND device through a NAND interface (NI) in the controller (see FIG. 5). According to an embodiment of the invention it may be desirable to modify the NAND interface unit in the NAND controller such that the NI unit (NI) performs the required bitwise replacement operation.

Note that the NI works by transferring the data byte by byte or word by word. The NAND device is unaware of the fact that there are bad columns or of the content of the data. Any of the replacement operations are performed by the NI without modifying the standard operation of the NAND device.

#### Bit Skipping

While sending the aggregated codewords to the NAND Flash, the NI unit is loaded with the list of all bad columns in the NAND Flash die. Each time a bit is going to be written to a bad column, a dummy bit is inserted in place of the original data and the original bit stream from that point on is shifted by one bit. Thus, the original data is not written to bad columns. Similarly, when reading data from the NAND, each time a bad column is encountered, the corresponding bit is overrun with the next bit being read. All the following bits are shifted to replace the columns being overrun. FIG. 6 shows an example of a mapping between a concatenated codeword 60 and the physical page 61.

Note that throughout we assume that the amount of data in the concatenated codewords is less than in the physical page, to make room for bad columns. However, there may be two cases that need to be taken into account:

Case one—the amount of bits in the concatenated codewords+the number of bad columns is still smaller than the physical page size. In that case, during the programming operation, additional dummy bits are inserted (e.g. zeros) at the end of the stream to complete it to a physical page size.

Case two—the amount of bits in the concatenated codewords+the number of bad columns is still greater than the physical page size. In that case, during programming the data bits which overrun the page are truncated. During the read operation missing data, bits are padded with zeros, causing some errors in those bits.

Whether case one or case two are relevant depend on the size of the codeword redundancy and the number of bad columns. The codeword redundancy can be chosen by the designer of the NAND Flash controller. However, the number of bad columns in a NAND device is random and changes between one device and another. The manufacturer guarantees that the maximum number of bad columns will not exceed a certain maximum but this is typically much larger than the actual number of bad columns. Therefore, the size of the redundancy may be chosen as a function of the distribution of bad columns.

Another note on the choice of the dummy bits: the dummy bit may be chosen to have the value of the original bit intended to be written to the bad column. If a bad column is not completely bad, the read information from that bit can be used to obtain additional information and increase reliability.

#### Bit Replacement

Bit skipping may be difficult to implement in hardware as the streaming data becomes unaligned with the standard units

of bytes/words/double words. This alignment is important as it eases the job of parallelizing in streamlining the operation of the unit.

Therefore, in the following we present a hardware implementation of a unit that does not perform bit skipping but rather bit replacement. In this scheme, data bits that fall on bad columns are copied into a spare register, which then appended to the data stream and programmed last to the NAND page. During read, the last bytes, which contain the spare register, are read first.

Under some cases, the read operation may first be attempted without reading the spare register. In that case, the information that was read from the bad columns can be used. Only upon decoding failure we may choose to read the spare register bits. The cases that may be of interest are those where data is being read from random location which will cause the NI unit to take longer time to read, if it needs to perform replacement.

#### Hardware Implementation

FIG. 5 illustrates system 300 according to an embodiment of the invention. It may include memory controller 333 and NAND flash memory unit 390. The memory controller 333 may include a control circuit 310 and a NAND interface unit (NI) 350. The control circuit 310 may include encoder/decoder 312, a read circuit 320, write circuit 330, a determination circuit 360, and a memory unit 340.

The NAND flash memory unit 390 includes an internal controller 380 and NAND flash memory array 370. It may include multiple arrays, one or more flash memory dies, one or more planes, and the like. The internal controller 380 may program data to the NAND flash memory array 370, may read data from the NAND flash memory array 370 and may erase the NAND flash memory array 370—under the control of instructions sent from the memory controller 333 (via NU 350).

The determination circuit 360 may receive or generate column error statistics may determine how to respond to column error statistics, may determine an encoding scheme and the like. Encoder/decoder 312 may encode and/or decode data, append redundancy bits and the like.

FIGS. 8-10 illustrate portions of the memory controller 333 according to various embodiments of the invention.

Bad columns detection information is gathered and saved in BCM—Bad Column Memory (say implemented in Random Access Memory) 340(2) that is accessible by the NI unit and holds the data required for bits replacement. Each line of this memory holds:

- Pointer to a Word (say 16 bits) in a page that holds at least 1 bad column.
- Bit mask (16 bits for example) that specifies the bad bit within this Word.

The number of BCM lines should equal to the maximal number of bad columns that is guaranteed by the manufacturer.

As bad column is a bit line defect, same bits should be replaced in all pages that use the same sense amplifier (typically a Flash Plane). Hence, a single BCM database may be sufficient to replace all bad columns in this Flash Plane. If the Flash device consists of multiple planes, multiple BCMs are required.

FIG. 8 describes the implementation of Flash page program circuit with bad bits replacement. Normally, data (aggregated codewords) streams in from a page buffer 340(1) within a memory unit 340 of a control circuit 310 of memory controller 333, into NI unit port 101 and address counter 102 counts each Word that is sent to the NAND flash memory unit 390. The invention suggests another BCM address counter

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103 to point the BCM relevant line, this counter is initiated to the value "0" before each program operation begins. Data begins to flow from data in port 101 to the flash device while page address counter 102 counts the outgoing Words. Once the page address counter 102 reaches the first Word that consists a bad column (equals first word pointer 211(0)), "bad column accessed logic" output wire 104 is asserted driving the input of the AND gate 105 high. The first bit mask 212(0) is present on the other input of AND gate 105. AND gate 105 is duplicated for each bit in the Word (say 16 bits—i.e. gates 105.0-105.15). The outputs of AND gates 105 cause relevant bits of data in bus 101 to be shifted into the spare register 106. The bit size of the spare register should equal the maximal number of bad columns that manufacturer guarantees. Single or multiple bits may be asserted on the bit mask bus, and so single or multiple bits may be shifted into the spare register each clock cycle in a LSB→MSB order. Since wire 104 is asserted, the BCM address counter 103 (line pointer) is incremented. The data continues flowing through the NI unit, page address counter 102 continues running, and when it equals the next Word pointer 211(1), data in bus bits are replaced according to bit mask 212(1) and BCM address 103 is incremented again.

This flow continues until all aggregated codewords were driven in from the page buffer 340(1). At this time page address comparator 107 output pin is asserted causing spare register 106 to shift out a Word each clock cycle. Meanwhile, the select to data MUX 108 select signal is also set causing data from spare register 106 to flow in the NAND Flash memory unit 390 direction on the data bus. During shift data out of spare register 106, zeros may be shifted in (for end zeros padding). The flow ends when the number of Words sent to the Flash device equals the page size.

Note that bad columns may be present in the spare area (end of the Flash page). As this area is relatively small compared to the page size, not replacing those bits will probably not add many error to the programmed page, and when reading, those errors can be fixed by error correction circuitry. However, those bits can be replaced during program operation as long as the Flash page size is no smaller than the sum of aggregated codewords and the maximum bad columns.

FIG. 9 describes the implementation of Flash page read circuit with bad bits replacement. Normally, Flash page data comes in from NAND flash memory unit 390 on data bus 401 single Word (say 16 bits) at a clock cycle and driven to page buffer 340(1) on data bus 111. The transaction ends when page size Words were read. The invention suggests replacement of the bad column bits by the NI unit 350, meaning that aggregated codewords+spare bits stream in from the NAND Flash memory unit 390 and only aggregated codewords stream out to page buffer 340(1).

NAND Flash interface protocol allows reading from any desired Word offset of the page register 410 in the NAND Flash memory unit 390 that holds the latched array data.

When the controller signals to start reading, a finite state machine (FSM 120) is responsible to first read the spare area of the page register and later the aggregated codewords.

Spare area read FSM 120 controls the Flash page offset setting by using address setting circuitry 130. At first FSM 120 sets the page register 410 read pointer to offset 411. FSM 120 also activates page address counter 102 (via interface 121) to count Words starting at the spare page area, thus page address comparator 107 result is asserted (counter greater than aggregated codewords). Assertion of this signal causes on one hand incoming data Words on data bus 401 to be shifted into spare register 106, and on the other hand enable circuitry 110 to block data from being driven to page buffer

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340(1). When page address counter 102 reaches page end it signals FSM 120 "spare read done" via interface 122.

Aggregated codewords read FSM 120 then sets Flash device page register offset to 411 (typically 0) and activates page address counter 102 again (via interface 123) to start counting from the value set in page register 410 to offset 412. At this stage BCM address counter 103 is set to 0, thus pointing the first BCM line. Page data starts streaming in and page address counter 102 counts each incoming Word. Once page counter 102 reaches the BCM output 211(0) (selected word\_ptr), "bad column accessed logic" output wire 104 is asserted.

Then:

- c. AND gates 105 drive logical "1" for any bit set on the current bit mask 212(0).
- d. The amount of "to be replaced bits" are shifted out of spare register 106.
- e. Bit mask 212(0) specified bits are replaced by MUX 109.
- f. BCM address (line pointer) counter 103 is incremented to point the next line.

Since page address counter was activated to count from page start, the data out circuitry 110 does not block the data out bus 111 that drives Word by Word to the page buffer 340(1).

In the next clock cycle the incoming the page address counter output 102 is again compared vs. the next BCM line Word pointer that is now present on the BCM output 211(0). Total amount of aggregated codewords is read from Flash memory unit 390 and by searching the BCM entries all bad columns are replaced.

Bad column located in the spare area can be replaced, more on that is described later.

FIG. 10 illustrates a portion 320(1) of a read circuit 320 capable of random access reading of codewords according to an embodiment of the invention.

Sometimes the system needs to read only a portion of a Flash page. As the Flash page holds ECC codewords this random read is aligned to a codeword start (say second codeword out of four codewords in a page). In such a case, the relevant BCM pointers may start from another BCM line than line 0 (as some lines may hold pointers to bad columns in the first codeword).

Two methods are suggested to handle such cases:

- g. First method: the read flow in this case begins with regular spare area read, FSM 120 sets spare area page offset 411, and uses interfaces 121 and 122 to shift out the spare area bits. Then FSM 120 signals the BCM address counter 103 via interface 124 to scan the BCM until a Word pointer is within the relevant (in our example second) codeword boundaries. Each clock cycle the BCM line pointer is incremented by 1. During scanning phase irrelevant replacement bits (of first codeword in this example) may shift out of spare register 106 each cycle. Scanning phase is done when a BCM line with a Word pointer within the relevant codeword (or higher one) is reached. As a result "scan done" is signaled over interface 124 to FSM 120. From this point on, FSM 120 uses interface 123 to set Flash page offset to the desired codeword start 413, and reading is done with the desired length (single codeword or longer). Using this way the scanning stage is time consuming and may affect the system performance.

- h. Second method: We assume that random reads start from few constant offsets in a page (codewords starts) and that this start is aligned to Word resolution. In order to save previous method scanning time, it is suggested that another database is saved in the controller. This database "Codeword First Bad Bits Pointers" holds, per codeword

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The bit location of first replacing bit of the codeword in the spare area (I) First relevant BCM line for the read codeword (II).

Read flow is as follows.

FSM **120** sets the page Word offset **411**, using page address setting circuitry **130**, to the Word that holds the first replacing bit (I). FSM **120** then reads the spare area from this offset to the end of the page (or until all replacing bits for the relevant codewords are read). Note that it may be required to shift out some bits from spare register **106** since the first read Word from spare area may hold some bits of a codeword that is not being read.

Now FSM **120** loads BCM address counter **103** with the first relevant BCM line (II) via interface **124**. FSM **120** also sets the page offset in the Flash to Word **413** address setting circuitry via control bus **402**. From this point on, reading is done as in the data read phase of a whole page.

FIG. 7 is a flow chart of a method **500** according to an embodiment of the invention.

Method **500** may start by stage **510** of receiving or generating bad columns information indicative of bad columns of a NAND flash memory array of a NAND flash memory array.

The bad columns information has a column resolution—each column of the NAND flash memory array can be tagged as good or bad (or associated a reliability level that may have more than two possible values) based upon errors detected in flash memory cells that belong to these columns. This is a finer resolution than chunk based (multiple column) resolution.

The bad column information can be generated, for example, by method **400**.

Stage **510** may be followed by stage **520** of receiving an input data unit to be written to the NAND flash memory array.

The input data unit may include bad column mapped data bits that are mapped to flash memory cells that belong to bad columns of the NAND flash memory array. The input data unit may be, for example, a word of a page and the method may be repeated for each word of that page. The bad column mapped data bits may be referred in the following text (for example in relation to FIG. 8-10) as “spare bits.”

Stage **520** may be followed by stage **530** of detecting the bad column mapped data bits. Stage **530** may include storing the bad column mapped data bits in bad column mapped memory unit of the memory controller. This bad column mapped memory unit can be a shift register, can be volatile or non-volatile. It may be referred to (for example—in pages 8-10) as a “spare bits register”.

Stage **530** may include detecting the bad column mapped data bits in response to a first data structure that maps flash memory cells of bad columns to locations of bad column mapped data bits within the input data unit. FIGS. 8 and 9 illustrate an example of a first data structure that is stored in a bad column memory (BCM). It includes a bit map (that tags bad and good flash memory cells) for each word of a page.

FIG. 10 illustrates an example of a first data structure **210** and of a second data structure **220** that are stored in a bad column memory (BCM) **200**. The first data structure **210** includes a bit map (that tags bad and good flash memory cells) for each word of a page—bit maps **212(0)-212(x)** for  $x$  words **211(0)-211(x)** of a page. The second data structure **220** maps codewords **221(0)-221(y)** to (i) content of the second portion of the NAND flash memory array (**223(0)-223(y)**) and to (ii) entries of the first data structure (**222(0)-222(y)**).

Stage **530** may be followed by stage **540** of sending the input data unit to the NAND flash memory unit and instruct-

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ing the NAND flash memory unit to write the input data unit to a first portion of the NAND flash memory array to provide a programmed data unit.

Stage **540** may be followed by stage **550** of sending the bad column mapped data bits to the NAND flash memory unit. It is noted that the bad column mapped data can be stored on the NAND flash memory unit or in any other memory unit of any type. Furthermore, it may be stored once in the NAND flash memory unit in a particular location and not every time new data is written. It is then read only once, when the system starts up and a memory controller reads the bad column mapped data from the NAND flash memory unit.

Stage **550** may be followed by stage **560** of instructing the NAND flash memory unit to write the bad column mapped data bits to a second portion of the NAND flash memory array to provide programmed bad column mapped data bits. It is noted that the first and second portions can be programmed concurrently and can belong to a same page.

This second portion can be referred to as a spare area. The second portion can include bad columns or may be free of bad columns. If it includes bad columns than any of the schemes illustrated in this application (such as bit skipping) can be applied.

The first and second portions of the NAND flash memory array belong to a same physical page of the NAND flash memory array.

Stage **560** may be followed by either one of stages **570** and **572**.

Stage **570** includes reading the programmed bad column mapped data bits to provide read bad column mapped data bits.

Stage **572** may include reading from the first portion of the NAND flash memory unit the programmed input data unit to provide a read data unit.

Stage **572** may be followed by stage **574** of applying an error correction process on the read data unit to provide error correction results and determining whether to read the programmed bad column mapped data bits in response to the error correction results. If, for example, the error correction process corrected all the errors then there is no need in reading the programmed bad column mapped data bits.

If it is determined to read the programmed input data unit then stage **574** is followed by stage **570**—else it is followed by stage **580** of generating an output data unit in response to the read data unit and read bad column mapped data bits.

Stage **580** may include replacing bits of the read data unit that were mapped to flash memory units of bad columns by read bad column mapped data bits.

Stage **580** may include error correcting the read data unit using information obtained from the read bad column mapped data bits.

#### Bad Columns Spreading Schemes

Next we consider a different type of handling of bad columns. Bad-columns may be arbitrarily distributed in a device. Therefore, the bad columns may be unevenly distributed between the codewords. FIG. 11 shows an example of an imaginary page 80 with 32 bits with 4 bad columns—represented by black boxes in bits **4**, **19**, **25** and **31**. There are also 4 codewords (CWs) **71-74** in this example with CW **1** suffering from 1 bad column, CW **2** having no bad columns, CW **3** having 1 bad column and CW **4** having 2 bad columns. This means that CW **4** has a higher probability of decoding failure than the rest of the CWs. Furthermore, CW **2** has higher probability of decoding success than the others.

To even out the probability of decoding success, According to an embodiment of the invention it may be desirable to spreading the effect of the bad columns across the CWs. In

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FIG. 11 this is done by using one of the bits of CW2 to replace a bad column of CW4 and writing content of CW2 to the bad bit. Thus, before programming, bit 31 (in CW4) is copied to position 16 (in CW2) and the programming is performed. After reading the page, bit 16 is placed in the position of bit 31 and decoding is done for all 4 codewords. Effectively, each codeword has 1 “bad” bit, whether because of a real or virtual bad-column.

In general, to even out bad columns across codewords the scheme of FIG. 12 may be used. According to the method 20 of FIG. 12, good columns belonging to certain codewords are arbitrarily chosen to replace bad columns. However, we may choose these good columns such that if they were flipped to be bad columns their effect on decoding may be the least. The choice of such columns of course depends on the choice of the coding technique. Method 20 includes stages 21, 22, 23 and 24 and tries to spread bad flash memory cells between codewords—starting from replacing bits from a codeword that is mapped to a lowest number of bad bits with the bits from another codeword that is mapped to a highest number of bad bits.

Finally, the spreading scheme above does not include column replacement in the case where the total data in the codewords is smaller than the data in the page. The two schemes may be combined to create a joint replacement spreading scheme such that if the number of columns+the total number of bits in the concatenated codewords is larger than a page, the bad columns are evenly spread across the codewords.

#### Code Definition to Account for Bad Columns

In general, the number of bad columns in a NAND device is random and changes between one device and another. The manufacturer guarantees that the maximum number of bad columns will not exceed a certain maximum but this is typically much larger than the actual number of bad columns. Therefore, the size of the redundancy may be chosen as a function of the distribution of bad columns.

We can define a BER function of the code which is a function that defines the BER the code can handle given a certain amount of bad columns that were not replaced and given the available redundancy.

Example:  $Fber(Nred, Nbad\_columns) = A * Nred - B * Nbad\_columns$ .

a. Nred=number of redundancy bits

b. Nbad columns=number of bad columns that were not replaced

A and B are parameters that approximate the capability of the code. The code may be BCH, BCH with erasure and the like, LDPC with hard or soft or erasure decoding.

Other examples of BER functions are also possible.

In addition, we also define a function that relates between the distribution of bad columns and the redundancy of a code word.

Example:

a.  $P_{reduced\_bad\_columns}(k, Nred) = P_{bad\_columns}(k')$ .

b.  $k' = k + Nred - C$ .

c.  $P_{bad\_columns}(k')$  is the distribution of the number of bad columns across dies of the flash memory unit and C is some constant.

Other examples of distributions are also possible.

Therefore, given the above distribution and BER functions we can optimize the choice of redundancy to maximize a score function. Examples:

a. Maximize average handled BER, wherein the average handled BER equals a sum (over k values ranging from zero to a maximal number of errors) of  $P_{reduced\_bad\_columns}(k, Nred)$  multiplied by  $Fber(Nred, k)$ .

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b. Maximize BER under an outage probability limitation so that the chosen redundancy is maximized such that the sum of  $P_{reduced\_bad\_columns}(k, Nred)$  over k greater than 0 is still smaller than some limit (Outage limit).

$$\begin{aligned} &\text{maximize} && n_{red} \\ &\text{s.t.} && P_{reduced\_bad\_columns}(k > 0, n_{red}) \leq \text{Outage limit} \end{aligned}$$

#### Adaptive Code Definition Upon Device Initialization

Another alternative is to define the code redundancy upon controller initialization. A controller is always coupled with a set of devices. Once the devices are chosen, the bad columns are fixed. Therefore, the redundancy may be adapted to that bad columns configuration such as to replace all bad columns and thus maximize the handled BER for that die configuration.

Note that the redundancy may be configured only to a predefined set of values. In that case the redundancy is chosen for a given die configuration to maximize  $Fber(Nred, Nbad\_columns + Nred - C)$ .

#### Concatenated Dies

In some systems data is written on several NAND flash dies and codewords may be programmed across two dies (first part of a codeword on one die and the last part of the codeword on another die) or even more than two dies. In this case, we can think of several dies as one super die and add up all the bad columns together and apply all the algorithms above (bit skipping, replacement, etc.) to the super die instead of a single die. Furthermore, we can apply the redundancy selection methods above to the super die rather than a single die. This allows improving some of the results since now the number of bad columns is effectively averaged over several dies.

The invention may also be implemented in a computer program for running on a computer system, at least including code portions for performing steps of a method according to the invention when run on a programmable apparatus, such as a computer system or enabling a programmable apparatus to perform functions of a device or system according to the invention. The computer program may cause the storage system to allocate disk drives to disk drive groups.

A computer program is a list of instructions such as a particular application program and/or an operating system. The computer program may for instance include one or more of: a subroutine, a function, a procedure, an object method, an object implementation, an executable application, an applet, a servlet, a source code, an object code, a shared library/dynamic load library and/or other sequence of instructions designed for execution on a computer system.

The computer program may be stored internally on a non-transitory computer readable medium. All or some of the computer program may be provided on computer readable media permanently, removably or remotely coupled to an information processing system. The computer readable media may include, for example and without limitation, any number of the following: magnetic storage media including disk and tape storage media; optical storage media such as compact disk media (e.g., CD-ROM, CD-R, etc.) and digital video disk storage media; nonvolatile memory storage media including semiconductor-based memory units such as FLASH memory, EEPROM, EPROM, ROM; ferromagnetic digital memories; MRAM; volatile storage media including registers, buffers or caches, main memory, RAM, etc.

A computer process typically includes an executing (running) program or portion of a program, current program values and state information, and the resources used by the operating system to manage the execution of the process. An operating system (OS) is the software that manages the sharing of the resources of a computer and provides programmers with an interface used to access those resources. An operating system processes system data and user input, and responds by allocating and managing tasks and internal system resources as a service to users and programs of the system.

The computer system may for instance include at least one processing unit, associated memory and a number of input/output (I/O) devices. When executing the computer program, the computer system processes information according to the computer program and produces resultant output information via I/O devices.

In the foregoing specification, the invention has been described with reference to specific examples of embodiments of the invention. It will, however, be evident that various modifications and changes may be made therein without departing from the broader spirit and scope of the invention as set forth in the appended claims.

Moreover, the terms "front," "back," "top," "bottom," "over," "under" and the like in the description and in the claims, if any, are used for descriptive purposes and not necessarily for describing permanent relative positions. It is understood that the terms so used are interchangeable under appropriate circumstances such that the embodiments of the invention described herein are, for example, capable of operation in other orientations than those illustrated or otherwise described herein.

The connections as discussed herein may be any type of connection suitable to transfer signals from or to the respective nodes, units or devices, for example via intermediate devices. Accordingly, unless implied or stated otherwise, the connections may for example be direct connections or indirect connections. The connections may be illustrated or described in reference to being a single connection, a plurality of connections, unidirectional connections, or bidirectional connections. However, different embodiments may vary the implementation of the connections. For example, separate unidirectional connections may be used rather than bidirectional connections and vice versa. Also, plurality of connections may be replaced with a single connection that transfers multiple signals serially or in a time multiplexed manner. Likewise, single connections carrying multiple signals may be separated out into various different connections carrying subsets of these signals. Therefore, many options exist for transferring signals.

Although specific conductivity types or polarity of potentials have been described in the examples, it will be appreciated that conductivity types and polarities of potentials may be reversed.

Each signal described herein may be designed as positive or negative logic. In the case of a negative logic signal, the signal is active low where the logically true state corresponds to a logic level zero. In the case of a positive logic signal, the signal is active high where the logically true state corresponds to a logic level one. Note that any of the signals described herein may be designed as either negative or positive logic signals. Therefore, in alternate embodiments, those signals described as positive logic signals may be implemented as negative logic signals, and those signals described as negative logic signals may be implemented as positive logic signals.

Furthermore, the terms "assert" or "set" and "negate" (or "deassert" or "clear") are used herein when referring to the rendering of a signal, status bit, or similar apparatus into its

logically true or logically false state, respectively. If the logically true state is a logic level one, the logically false state is a logic level zero. And if the logically true state is a logic level zero, the logically false state is a logic level one.

Those skilled in the art will recognize that the boundaries between logic blocks are merely illustrative and that alternative embodiments may merge logic blocks or circuit elements or impose an alternate decomposition of functionality upon various logic blocks or circuit elements. Thus, it is to be understood that the architectures depicted herein are merely exemplary, and that in fact many other architectures may be implemented which achieve the same functionality.

Any arrangement of components to achieve the same functionality is effectively "associated" such that the desired functionality is achieved. Hence, any two components herein combined to achieve a particular functionality may be seen as "associated with" each other such that the desired functionality is achieved, irrespective of architectures or intermedial components. Likewise, any two components so associated can also be viewed as being "operably connected," or "operably coupled," to each other to achieve the desired functionality.

Furthermore, those skilled in the art will recognize that boundaries between the above described operations merely illustrative. The multiple operations may be combined into a single operation, a single operation may be distributed in additional operations and operations may be executed at least partially overlapping in time. Moreover, alternative embodiments may include multiple instances of a particular operation, and the order of operations may be altered in various other embodiments.

Also for example, in one embodiment, the illustrated examples may be implemented as circuitry located on a single integrated circuit or within a same device. Alternatively, the examples may be implemented as any number of separate integrated circuits or separate devices interconnected with each other in a suitable manner.

Also for example, the examples, or portions thereof, may be implemented as soft or code representations of physical circuitry or of logical representations convertible into physical circuitry, such as in a hardware description language of any appropriate type.

Also, the invention is not limited to physical devices or units implemented in non-programmable hardware but can also be applied in programmable devices or units able to perform the desired device functions by operating in accordance with suitable program code, such as mainframes, minicomputers, servers, workstations, personal computers, notepads, personal digital assistants, electronic games, automotive and other embedded systems, cell phones and various other wireless devices, commonly denoted in this application as 'computer systems'.

However, other modifications, variations and alternatives are also possible. The specifications and drawings are, accordingly, to be regarded in an illustrative rather than in a restrictive sense.

In the claims, any reference signs placed between parentheses shall not be construed as limiting the claim. The word 'comprising' does not exclude the presence of other elements or steps than those listed in a claim. Furthermore, the terms "a" or "an," as used herein, are defined as one or more than one. Also, the use of introductory phrases such as "at least one" and "one or more" in the claims should not be construed to imply that the introduction of another claim element by the indefinite articles "a" or "an" limits any particular claim containing such introduced claim element to inventions containing only one such element, even when the same claim

includes the introductory phrases “one or more” or “at least one” and indefinite articles such as “a” or “an.” The same holds true for the use of definite articles. Unless stated otherwise, terms such as “first” and “second” are used to arbitrarily distinguish between the elements such terms describe. Thus, these terms are not necessarily intended to indicate temporal or other prioritization of such elements. The mere fact that certain measures are recited in mutually different claims does not indicate that a combination of these measures cannot be used to advantage.

While certain features of the invention have been illustrated and described herein, many modifications, substitutions, changes, and equivalents will now occur to those of ordinary skill in the art. It is, therefore, to be understood that the appended claims are intended to cover all such modifications and changes as fall within the true spirit of the invention.

I claim:

1. A method for managing bad columns of a NAND flash memory array of a NAND flash memory unit, the method comprises:

receiving or generating bad columns information indicative of the bad columns of the NAND flash memory array on a column to column basis;

receiving an input data unit to be written to the NAND flash memory array; wherein the input data unit comprises bad column mapped data bits that are mapped to flash memory cells that belong to the bad columns of the NAND flash memory array;

sending the input data unit to the NAND flash memory unit and instructing the NAND flash memory unit to write the input data unit to a first portion of the NAND flash memory array to provide a programmed data unit;

sending the bad column mapped data bits to the NAND flash memory unit; and

instructing the NAND flash memory unit to write the bad column mapped data bits to a second portion of the NAND flash memory array to provide programmed bad column mapped data bits; and

wherein the first and second portions of the NAND flash memory array belong to a same physical page of the NAND flash memory array.

2. The method according to claim 1 comprising storing the bad column mapped data bits at a bad column mapped memory unit of a memory controller.

3. The method according to claim 1 comprising detecting the bad column mapped data bits in response to a first data structure that maps the flash memory cells of bad columns to locations of the bad column mapped data bits within the input data unit.

4. The method according to claim 1 comprising storing at the NAND flash memory unit a first data structure that maps the flash memory cells of the bad columns to locations of the bad column mapped data bits and a second data structure that maps codewords to (i) content of the second portion of the NAND flash memory array and to (ii) entries of the first data structure.

5. The method according to claim 1 comprising reading from the first portion of the NAND flash memory unit the programmed input data unit to provide a read data unit; applying an error correction process on the read data unit to provide error correction results; and determining whether to read the programmed bad column mapped data bits in response to the error correction results.

6. The method according to claim 5 comprising reading the programmed bad column mapped data bits to provide read

bad column mapped data bits; and generating an output data unit in response to the read data unit and the read bad column mapped data bits.

7. The method according to claim 6 wherein the generating comprises replacing bits of the read data unit that were mapped to flash memory units of bad columns by the read bad column mapped data bits.

8. The method according to claim 6, comprising detecting bits of the read data unit that were mapped to flash memory units of bad columns by accessing a first data structure that maps flash memory cells of bad columns to locations of bad column mapped data bits within the input data unit.

9. The method according to claim 6, wherein the read data unit is associated with a certain codeword out of multiple codewords; wherein the method comprising detecting bits of the read data unit that belong to the certain codeword by accessing a first data structure that maps flash memory cells of bad columns to locations of bad column mapped data bits and by accessing a second data structure that maps codewords to (i) content of the second portion of the NAND flash memory array and to (ii) entries of the first data structure.

10. A non-transitory computer readable medium that stores instructions to be executed by a computer and cause the computer to perform stages comprising:

receiving or generating bad columns information indicative of bad columns of a NAND flash memory array of a

NAND flash memory unit on a column to column basis;

receiving an input data unit to be written to the NAND flash memory array; wherein the input data unit comprises bad column mapped data bits that are mapped to flash memory cells that belong to the bad columns of the NAND flash memory array;

sending the input data unit to the NAND flash memory unit and instructing the NAND flash memory unit to write the input data unit to a first portion of the NAND flash memory array to provide a programmed data unit;

sending the bad column mapped data bits to the NAND flash memory unit;

instructing the NAND flash memory unit to write the bad column mapped data bits to a second portion of the NAND flash memory array to provide programmed bad column mapped data bits; and

wherein the first and second portions of the NAND flash memory array belong to a same physical page of the NAND flash memory array.

11. A system, comprising a memory controller that comprises a control circuit and an interface;

wherein the control circuit is arranged to receive or generate bad columns information indicative of bad columns of the NAND flash memory array on a column to columns basis;

wherein the memory controller is arranged to receive an input data unit to be written to the NAND flash memory array; wherein the input data unit comprises bad column mapped data bits that are mapped to flash memory cells that belong to the bad columns of the NAND flash memory array;

wherein the interface is arranged to:

send the input data unit to the NAND flash memory unit; instruct the NAND flash memory unit to write the input data unit to a first portion of the NAND flash memory array to provide a programmed data unit;

send the bad column mapped data bits to the NAND flash memory unit;

instruct the NAND flash memory unit to write the bad column mapped data bits to a second portion of the

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NAND flash memory array to provide programmed bad column mapped data bits; and wherein the first and second portions of the NAND flash memory array belong to a same physical page of the NAND flash memory array.

12. The system according to claim 11 wherein the control circuit is arranged to store the bad column mapped data bits at a bad column mapped memory unit of the memory controller.

13. The system according to claim 11 wherein the control circuit is arranged to detect the bad column mapped data bits in response to a first data structure that maps the flash memory cells of the bad columns to locations of the bad column mapped data bits within the input data unit.

14. The system according to claim 11 wherein the control circuit is arranged to store at the NAND flash memory unit a first data structure that maps the flash memory cells of the bad columns to locations of the bad column mapped data bits and a second data structure that maps codewords to (i) content of the second portion of the NAND flash memory array and to (ii) entries of the first data structure.

15. The system according to claim 11 wherein the control circuit is arranged to read from the first portion of the NAND flash memory unit the programmed input data unit to provide a read data unit; apply an error correction process on the read data unit to provide error correction results; and determine whether to read the programmed bad column mapped data bits in response to the error correction results.

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16. The system according to claim 15 wherein the control circuit is arranged to read the programmed bad column mapped data bits to provide read bad column mapped data bits; and generate an output data unit in response to the read data unit and the read bad column mapped data bits.

17. The system according to claim 16 wherein the control circuit is arranged to generate the output data unit by replacing bits of the read data unit that were mapped to flash memory units of bad columns by read bad column mapped data bits.

18. The system according to claim 16, wherein the control circuit is arranged to detect bits of the read data unit that were mapped to flash memory units of bad columns by accessing a first data structure that maps flash memory cells of bad columns to locations of bad column mapped data bits within the input data unit.

19. The system according to claim 16, wherein the read data unit is associated with a certain codeword out of multiple codewords; wherein the control circuit is arranged to detect bits of the read data unit that belong to the certain codeword by accessing a first data structure that maps flash memory cells of bad columns to locations of bad column mapped data bits and by accessing a second data structure that maps codewords to (i) content of the second portion of the NAND flash memory array and to (ii) entries of the first data structure.

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